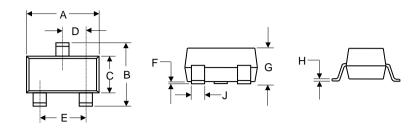


BAS19, BAS20, BAS21 Silicon Epitaxial Planar Diodes

Features

- * High Voltage Switching Diodes
- * Marking Code: HC











| SOT-23 | | | | | |
|--------|--------|-------|------|------|--|
| DIM | INCHES | | MM | | |
| | MIN | MAX | MIN | MAX | |
| А | 0.110 | 0.120 | 2.80 | 3.04 | |
| В | 0.087 | 0.102 | 2.20 | 2.60 | |
| С | 0.047 | 0.055 | 1.20 | 1.40 | |
| D | 0.035 | 0.04 | 0.89 | 1.02 | |
| E | 0.070 | 0.080 | 1.78 | 2.04 | |
| F | | 0.004 | | 0.10 | |
| G | 0.035 | 0.047 | 0.89 | 1.20 | |
| Н | 0.003 | 0.008 | 0.08 | 0.19 | |
| J | 0.015 | 0.02 | 0.37 | 0.51 | |

$\textbf{Maximum Ratings} \ \, (\text{T}_{\text{A}}\text{=-}25\,^{\circ}\text{C unless otherwise noted})$

| Parameter | Symbol | Value | Unit |
|--|------------------|-------------------|---------------|
| Reverse Voltage BAS19 BAS20 BAS21 | Vr | 120 200 250 | V |
| Continuous Forward Current | I F(AV) | 200 | mA |
| Repetitive Peak Forward Current | IFRM | 625 | mA |
| Non-repetitive Peak Forward Surge Current at t = 1 s at t = 1 µs | Ігѕм | 0.5 2.5 | А |
| Total Device Dissipation | P _{tot} | 350 | mW |
| Thermal Resistance Junction to Ambient | Reja | 357 | °C/W |
| Junction and Storage Temperature Range | Tj / Tstg | - 55 to + 150 | ${\mathbb C}$ |

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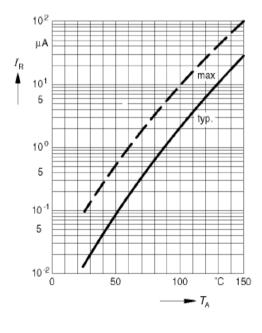
Electrical Characteristics (TA=25°C unless otherwise noted)

| Parameter | | Symbol | Min. | Max. | Unit |
|--|-------|-----------------|------|------|------|
| Forward Voltage | | | | | |
| at I _F = 100 mA | | VF | - | 1 | V |
| at I _F = 200 mA | | | - | 1.25 | V |
| Reverse Breakdown Voltage | | | | | |
| at I _R = 100 μA | BAS19 | Van | 120 | - | V |
| at I _R = 100 µA | BAS20 | V _{BR} | 200 | - | V |
| at I _R = 100 μA | BAS21 | | 250 | - | V |
| Reverse Current | | | | | |
| at V _R = 100 V | BAS19 | | - | 0.1 | μΑ |
| at V _R = 150 V | BAS20 | | - | 0.1 | μA |
| at V _R = 200 V | BAS21 | IR | - | 0.1 | μA |
| at V _R = 100 V, T _j = 150 °C | BAS19 | | - | 100 | μA |
| at V _R = 150 V, T _j = 150 ℃ | BAS20 | | - | 100 | μA |
| at V _R = 200 V, T _j = 150 °C | BAS21 | | - | 100 | μA |
| Total Capacitance | | 0 | | F | |
| at V _R = 0, f = 1 MHz | | Ctot | - | 5 | pF |
| Reverse Recovery Time | | trr | _ | 50 | ns |
| at If = IR= 30 mA, IR(REC) = 3 mA, RL = 100 Ω | | trr | _ | 30 | 113 |

Ratings and Characteristic Curves

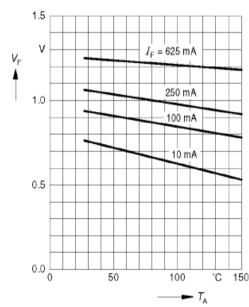
Reverse current $I_R = f(T_A)$

 $V_{\rm R} = 200 {\rm V}$



Forward Voltage $V_F = f(T_A)$

 I_{F} = Parameter



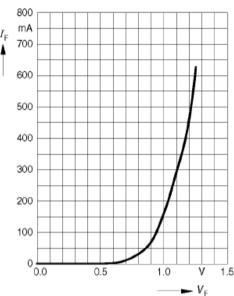
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BAS19, BAS20, BAS21 Silicon Epitaxial Planar Diodes

Ratings and Characteristic Curves





Ordering Information

| Part No. | Package | Packing Code | Packing |
|---------------------|---------|--------------|--------------|
| BAS19, BAS20, BAS21 | SOT-23 | R30 | 3000pcs/Reel |

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